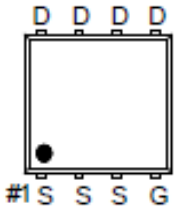
UNIKC Semiconductor

P1203BE

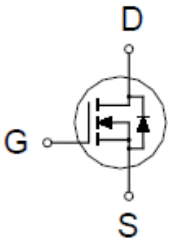
N-Channel Enhancement Mode MOSFET

PRODUCT SUMMARY

$V_{(BR)DSS}$	$R_{DS(ON)}$	I_D
30V	12mΩ @V_{GS} = 10V	9A



PDFN 3x3S



ABSOLUTE MAXIMUM RATINGS (T_A = 25 °C Unless Otherwise Noted)

PARAMETERS/TEST CONDITIONS		SYMBOL	LIMITS	UNITS
Drain-Source Voltage		V_{DS}	30	V
Gate-Source Voltage		V_{GS}	±20	
Continuous Drain Current	T_C = 25 °C	I_D	36	A
	T_C = 100 °C		22	
	T_A = 25 °C		9	
	T_A = 70 °C		7	
Pulsed Drain Current[1]		I_{DM}	108	
Avalanche Current		I_{AS}	28	
Avalanche Energy	L = 0.1mH	E_{AS}	39	mJ
Power Dissipation	T_C = 25 °C	P_D	25	W
	T_C = 100 °C		10	
	T_A = 25 °C		1.6	
	T_A = 70 °C		1	
Operating Junction & Storage Temperature Range		T_J, T_{STG}	-55 to 150	°C

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THERMAL RESISTANCE RATINGS

THERMAL RESISTANCE	SYMBOL	TYPICAL	MAXIMUM	UNITS
Junction-to-Ambient	$R_{\theta JA}$		75	°C / W
Junction-to-Case	$R_{\theta JC}$		3.6	

[1]Pulse width limited by maximum junction temperature.

ELECTRICAL CHARACTERISTICS (T_J = 25 °C, Unless Otherwise Noted)

PARAMETER	SYMBOL	TEST CONDITIONS	LIMITS			UNITS
			MIN	TYP	MAX	
STATIC						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	V_{GS} = 0V, I_D = 250μA	30			V
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = 250μA	1.3	1.8	2.5	
Gate-Body Leakage	I_{GSS}	V_{DS} = 0V, V_{GS} = ±20V			±100	nA
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = 24V, V_{GS} = 0V			1	μA
		V_{DS} = 20V, V_{GS} = 0V , T_J = 125 °C			10	
On-State Drain Current[1]	$I_{D(ON)}$	V_{DS} = 5V, V_{GS} = 10V	108			A
Drain-Source On-State Resistance[1]	$R_{DS(ON)}$	V_{GS} = 4.5V, I_D = 11A		13	17.5	mΩ
		V_{GS} = 10V, I_D = 11A		9	12	
Forward Transconductance[1]	g_{fs}	V_{DS} = 10V, I_D = 11A		22		S
DYNAMIC						
Input Capacitance	C_{iss}	V_{GS} = 0V, V_{DS} = 15V, f = 1MHz		843		pF
Output Capacitance	C_{oss}			210		
Reverse Transfer Capacitance	C_{rss}			115		
Gate Resistance	R_g	V_{GS} = 0V, V_{DS} = 0V, f = 1MHz		2.1		Ω
Total Gate Charge[2]	$Q_{g(VGS=10V)}$	V_{DS} = 0.5$V_{(BR)DSS}$, I_D = 11A		17.3		nC
	$Q_{g(VGS=4.5V)}$			9.2		
Gate-Source Charge[2]	Q_{gs}			2.7		
Gate-Drain Charge[2]	Q_{gd}			4.8		
Turn-On Delay Time[2]	$t_{d(on)}$	V_{DD} = 15V, $I_D \cong$ 11A, V_{GEN} = 10V, R_G = 6Ω		9.8		nS
Rise Time[2]	t_r			12.2		
Turn-Off Delay Time[2]	$t_{d(off)}$			9.7		
Fall Time[2]	t_f			11.7		

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SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS(T_J = 25 °C)						
Continuous Current	I_S				2.3	A
Forward Voltage[1]	V_{SD}	I_F = 11A, V_{GS} = 0V			1.3	V
Reverse Recovery Time	t_{rr}	I_F = 11A, dI_F/dt = 100A /μs		18		nS
Reverse Recovery Charge	Q_{rr}			8		nC

[1]Pulse test : Pulse Width ≤ 300 μsec, Duty Cycle ≤ 2%.

[2]Independent of operating temperature.

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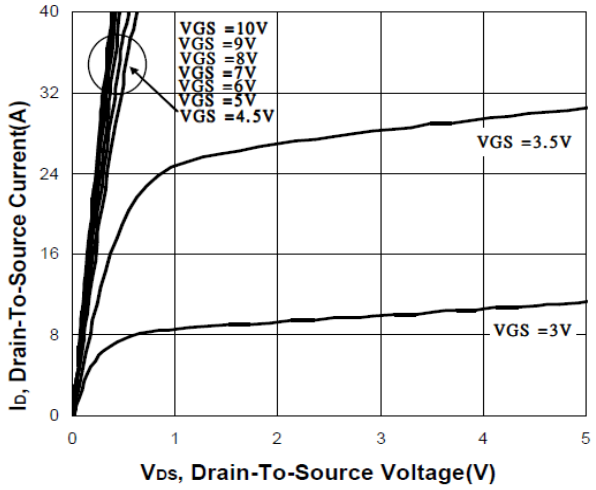
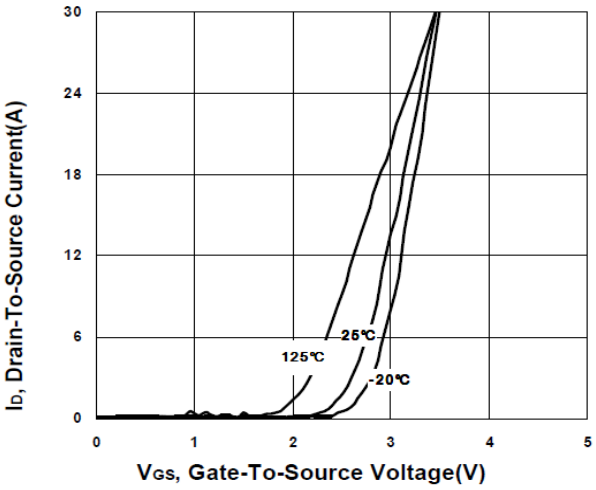
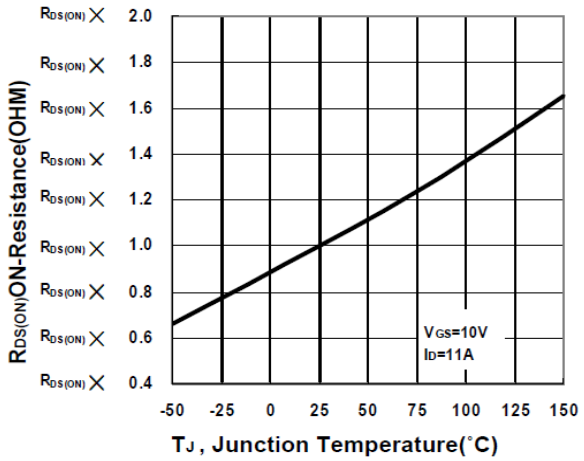
Output Characteristics



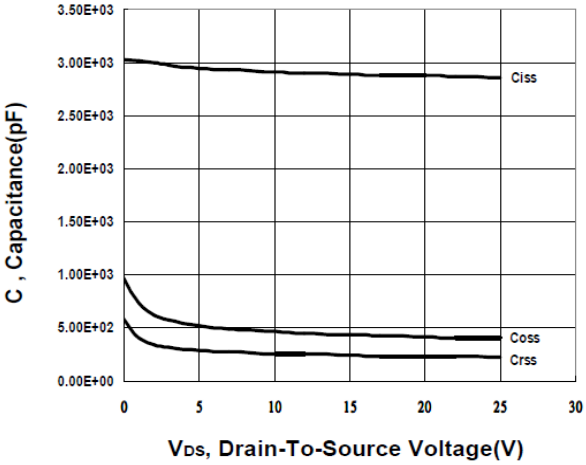
Transfer Characteristics



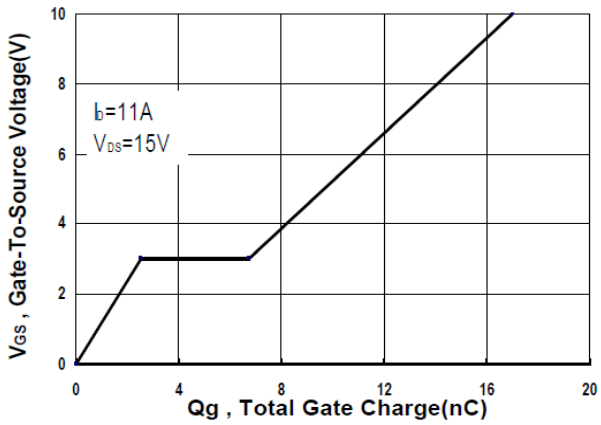
On-Resistance VS Temperature



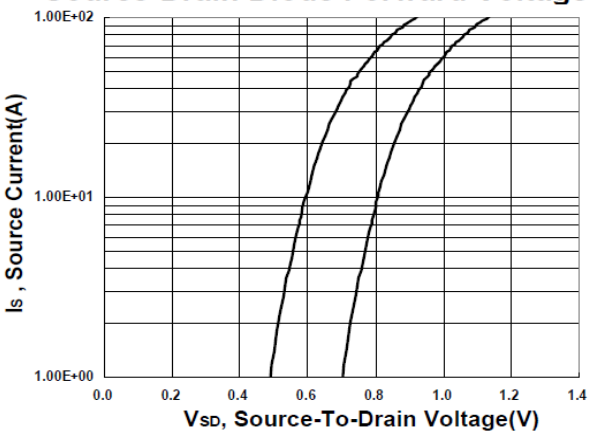
Capacitance Characteristic



Gate charge Characteristics



Source-Drain Diode Forward Voltage



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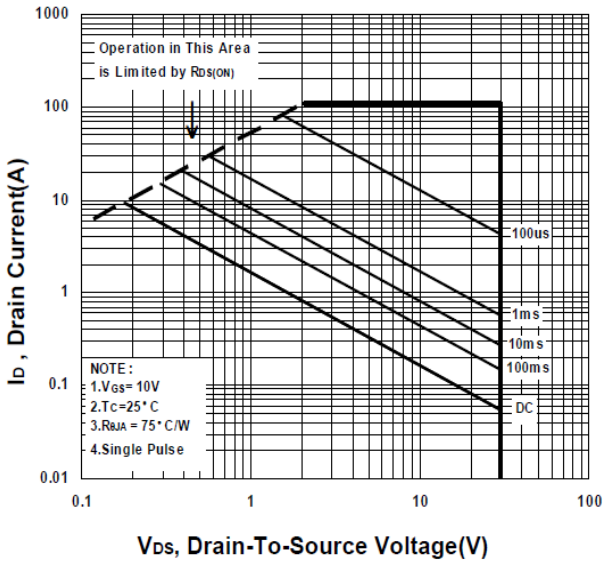
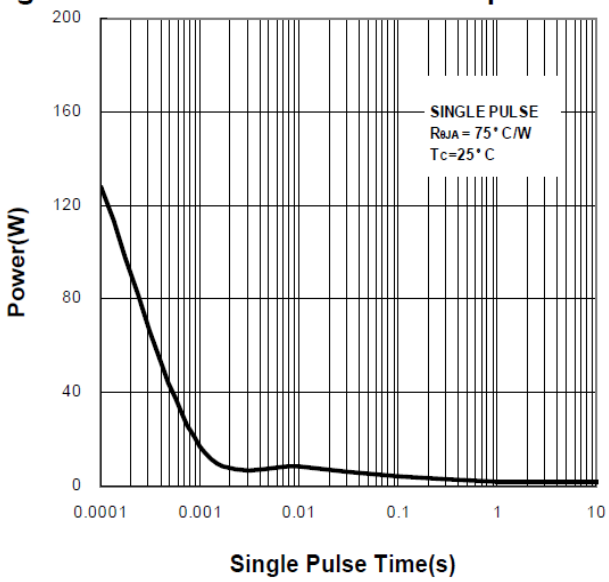
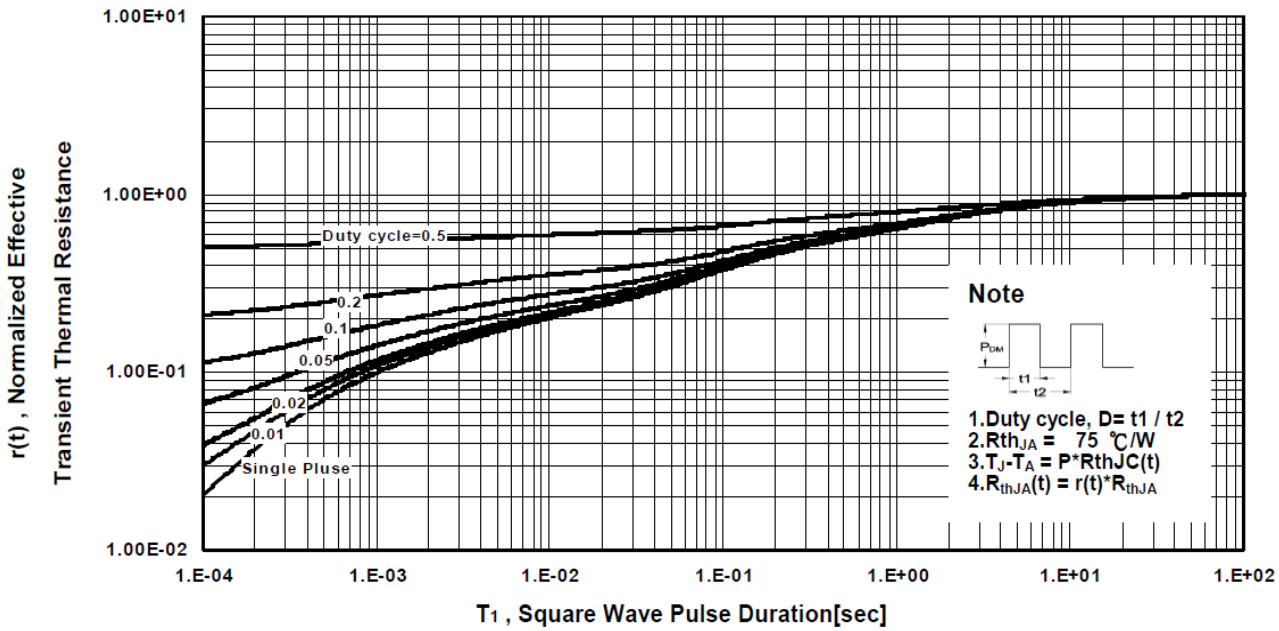
Safe Operating Area



Single Pulse Maximum Power Dissipation



Transient Thermal Response Curve



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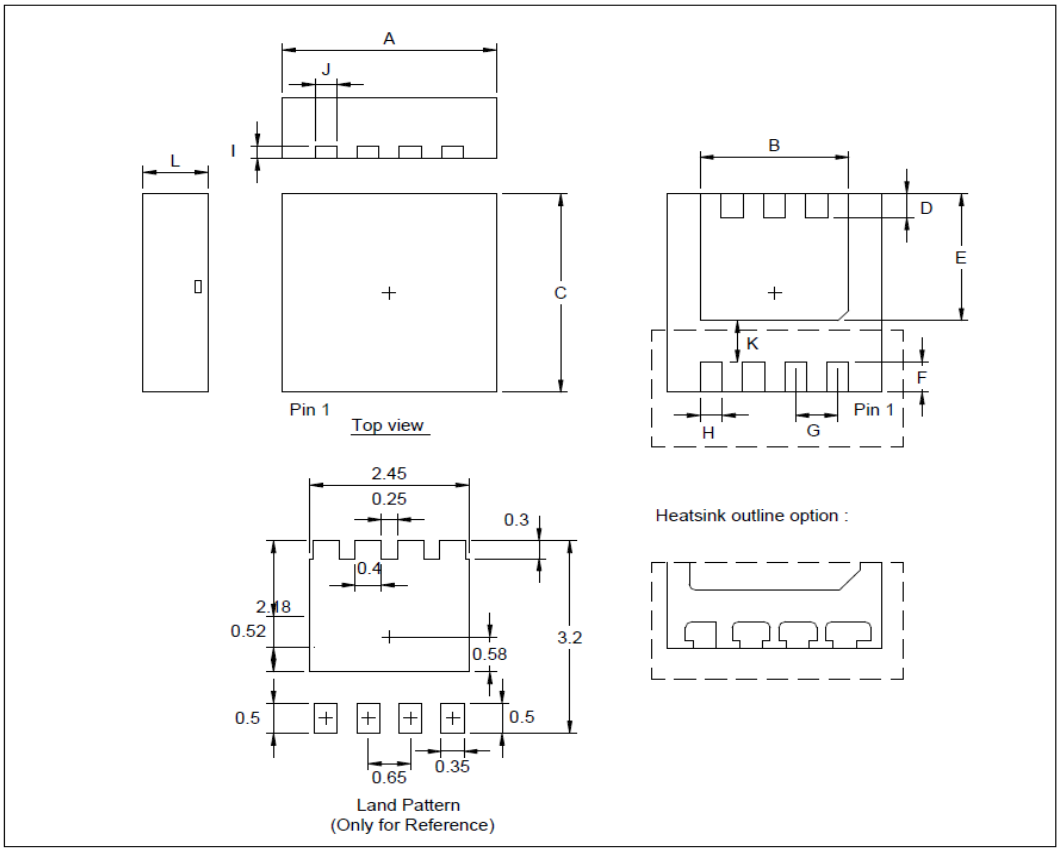
Package Dimension

PDFN 3x3S MECHANICAL DATA

Dimension	mm			Dimension	mm		
	Min.	Typ.	Max.		Min.	Typ.	Max.
A	2.9	3.0	3.1	I		0.20	
B	2.35	2.4	2.55	J	0.27	0.35	0.4
C	2.9	3.0	3.1	K		0.45	
D	0.32	0.4	0.45	L	0.7	0.8	0.9
E	2.0	2.1	2.2				
F	0.32	0.42	0.47				
G		0.65					
H	0.27	0.35	0.525				



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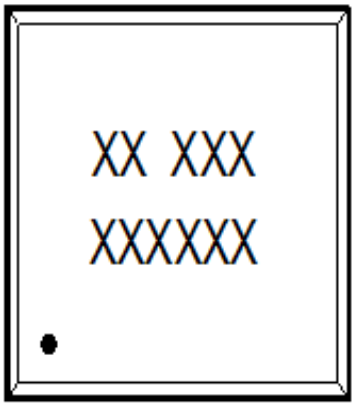
A. Marking Information(此产品代码为：A8)

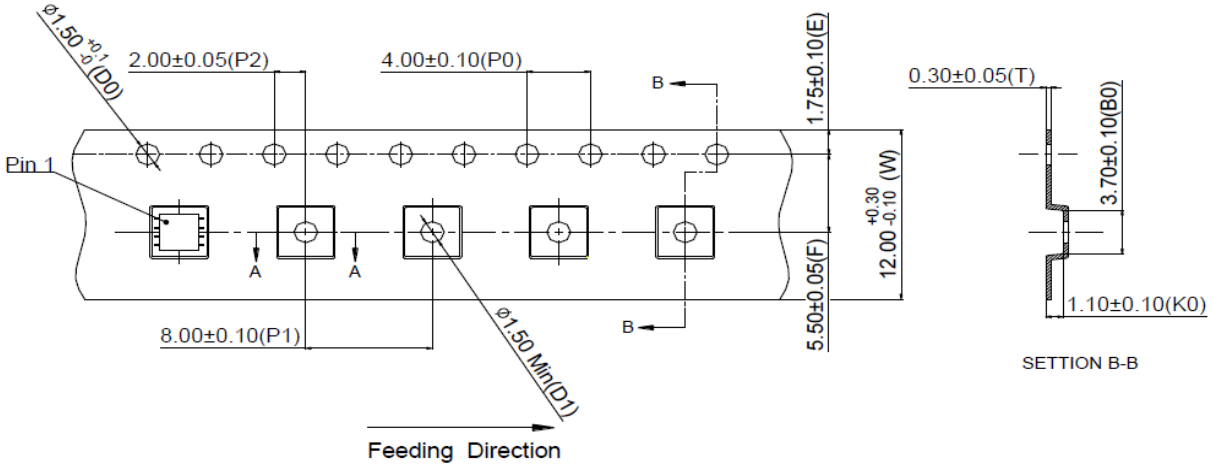


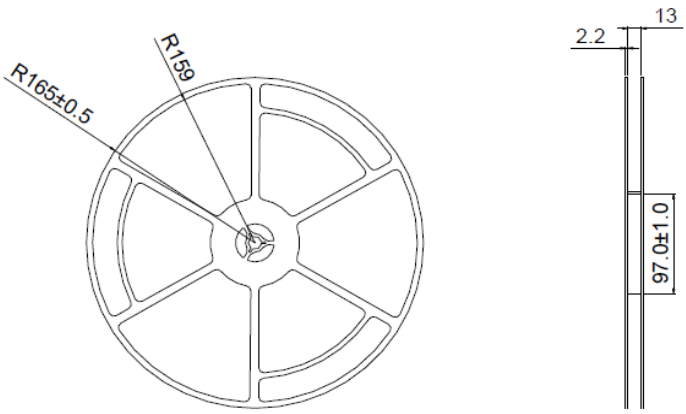
XX(前两码):产品代码

XXX

XXXXXX(后九码):LOT.NO

B. Tape&Reel Information:5000pcs/Reel





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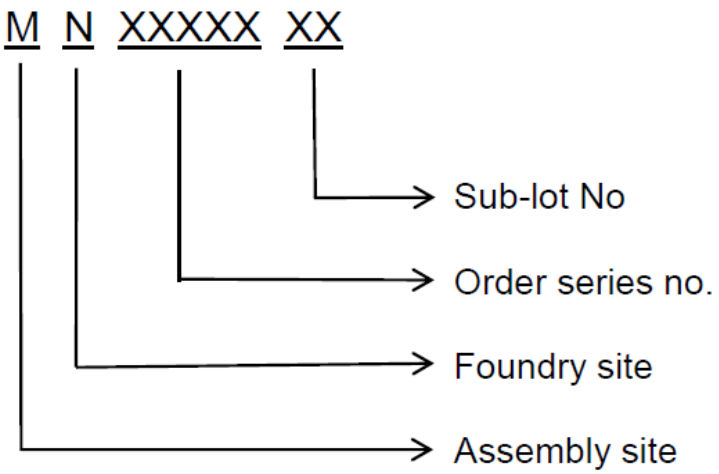
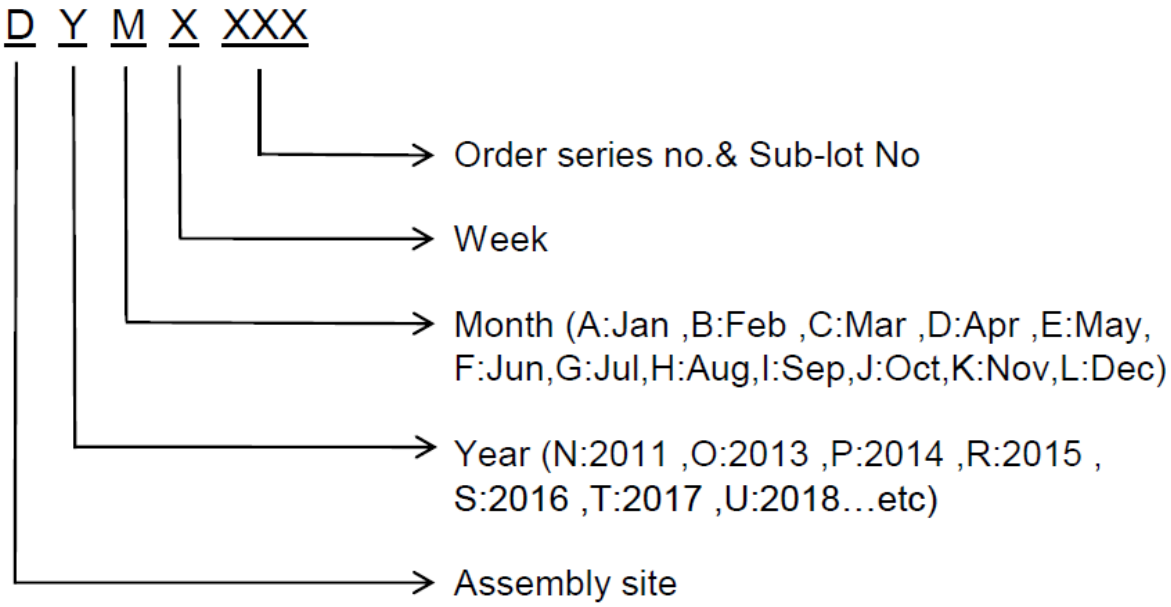
C. Lot No.&Date Code rule

1.Lot No.



2.Date Code



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D.Label rule

标签内容(Label content)

1	Label Size	30 * 90 mm
2	Font style	Times New Roman or Arial (或可区分英文”0”和数字”0”，”G和”Q”的字型即可)
3	U-NIKC	Height: 4 mm
4	Package	Height: 2 mm
5	Date	Height: 2 mm Shipping date: YYYY/MM/DD, ex. 2008/09/12
6	Device	Height: 3 mm (Max: 16 Digit)
7	Lot	Height: 3 mm (Max: 9 Digit) Sub lot
8	D/C	Height: 3 mm (Max: 7 Digit)
9	QTY	Height: 3 mm (Max: 6 Digit) Thousand mark is no needed
10	RoHS label	RoHS long axis: 12 mm minor axis:6 mm bottom color: White Font color: Black Font style: Arial
11	Halogen Free label	G Diameter: 10 mm bottom color: Green Font color: Black Font style: Arial
12	Scan information	Device / Lot / D/C / QTY , Insert “ / “ between every parts. for example: P3055LDG/G12345601/GGG2301/2000 DPI (Dots per inch): Over 300 dpi Code : Code 128 Height: 6 mm at least